ABSTRACT

CRYSTAL GROWTH METHOD FOR GROUP-III NITRIDE AND RELATED COMPOUND SEMICONDUCTORS

Crystals of group-III nitride and related compound semiconductors are grown on the surface of a periodic or nonperiodic multi-layered buffer in which the layers alternate between two types of compound semiconductors A and B, different from each other in lattice constant and energy band gap. The crystallinity of the group-III nitride and related compound semiconductors grown on the surface of such a multi-layered buffer can be significantly improved.

Fig.4 is to be published.